



STD150N3LLH6 STP150N3LLH6, STU150N3LLH6

N-channel 30 V, 0.0024 Ω , 80 A, DPAK, IPAK, TO-220
STripFET™ VI DeepGATE™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STD150N3LLH6	30 V	0.0028 Ω	80 A
STP150N3LLH6	30 V	0.0033 Ω	80 A
STu150N3LLH6	30 V	0.0033 Ω	80 A

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses

Application

- Switching applications

Description

This product utilizes the 6th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

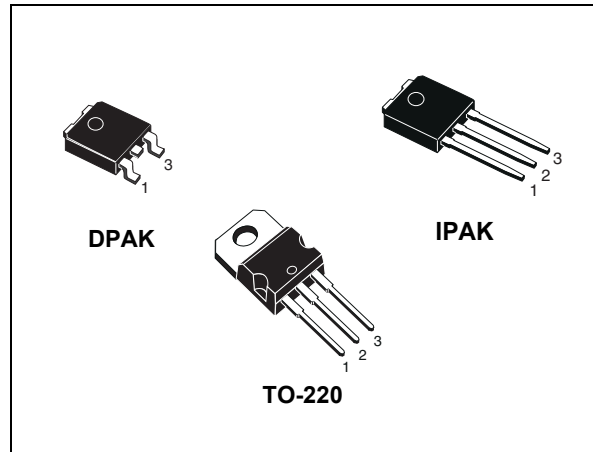


Figure 1. Internal schematic diagram

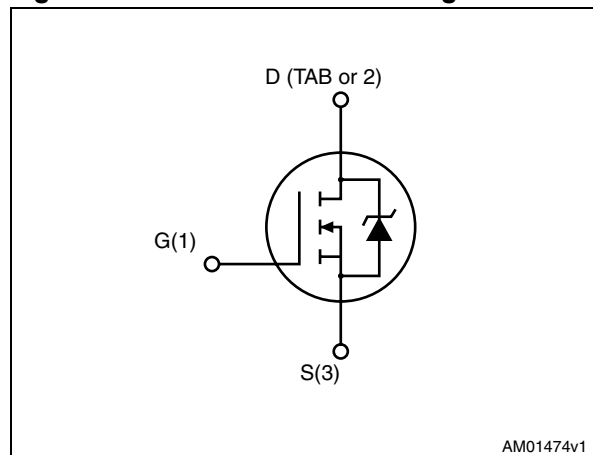


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD150N3LLH6	150N3LLH6	DPAK	Tape and reel
STP150N3LLH6	150N3LLH6	TO-220	Tube
STU150N3LLH6	150N3LLH6	IPAK	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
	Derating factor	0.73	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	525	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature	175	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 40\text{ A}$, $V_{DD} = 25\text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.36	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-case max	100	$^\circ\text{C}/\text{W}$
T_j	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}$, $T_c = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$ SMD version		0.0024	0.0028	Ω
		$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		0.0029	0.0033	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 40\text{ A}$ SMD version		0.0034	0.0045	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 40\text{ A}$		0.0039	0.0049	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	4040	-	pF
C_{oss}	Output capacitance			740		pF
C_{rss}	Reverse transfer capacitance			425		pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 80\text{ A}$	-	40	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 4.5\text{ V}$		16.3		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		15.8		nC
R_G	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain	-	1.4	-	Ω

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	17 18	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15)	-	75 46	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 24\text{ V}$ (see Figure 17)	-	34 35 2.1		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

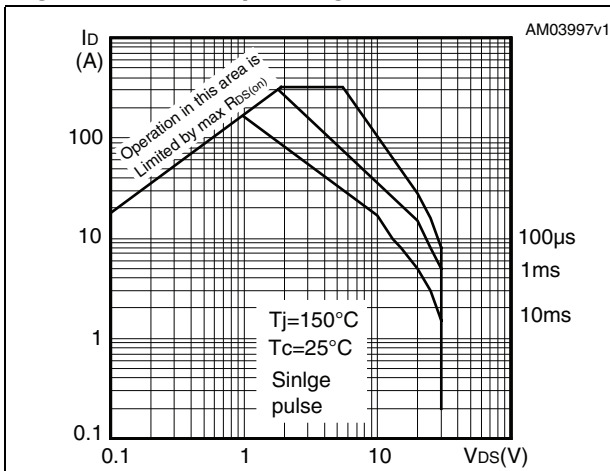


Figure 3. Thermal impedance

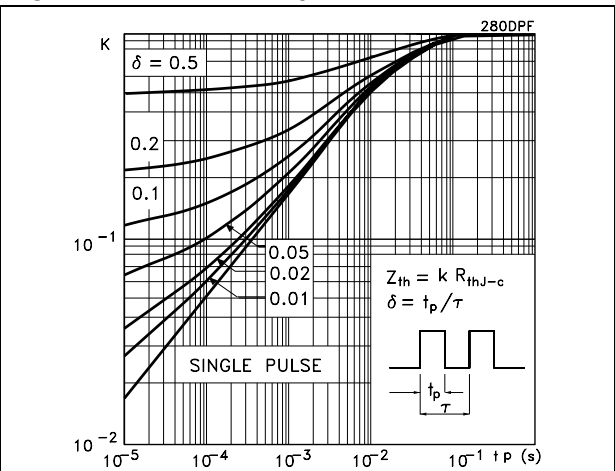


Figure 4. Output characteristics

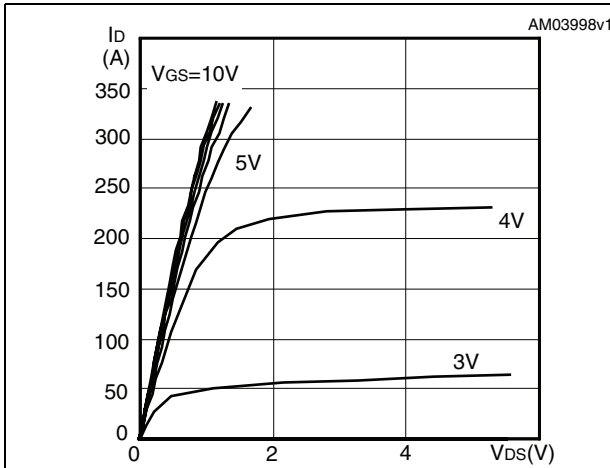


Figure 5. Transfer characteristics

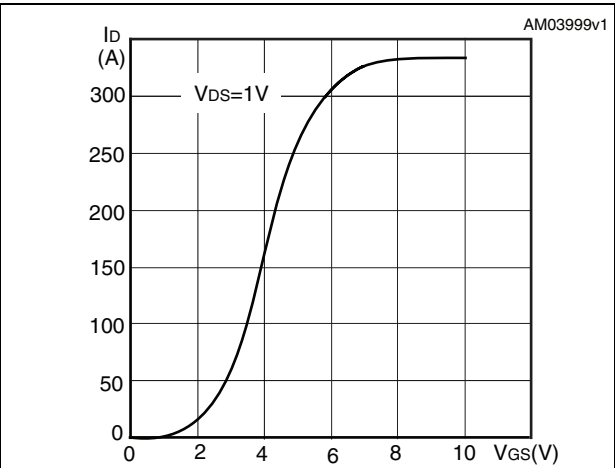


Figure 6. Normalized BV_{DSS} vs temperature

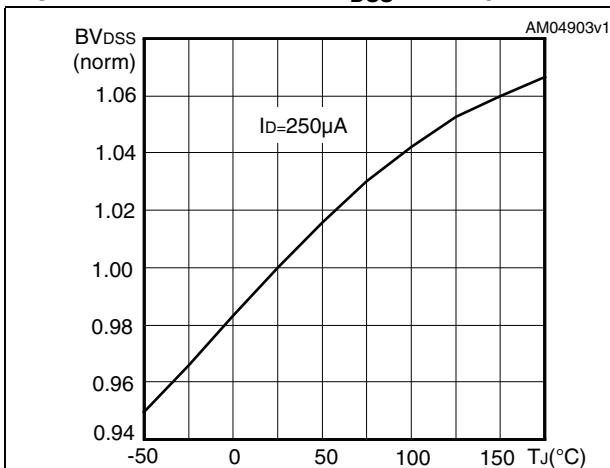


Figure 7. Static drain-source on resistance

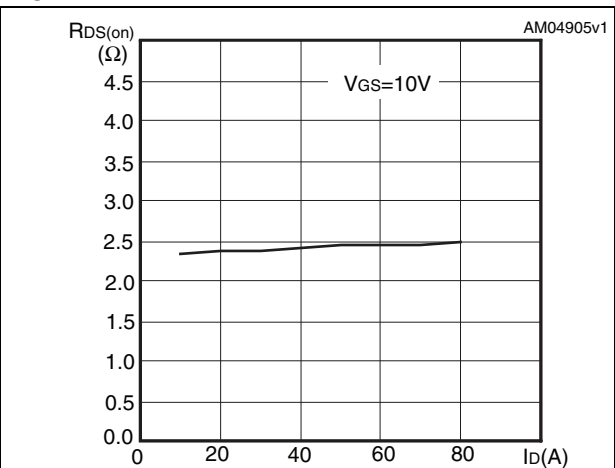


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

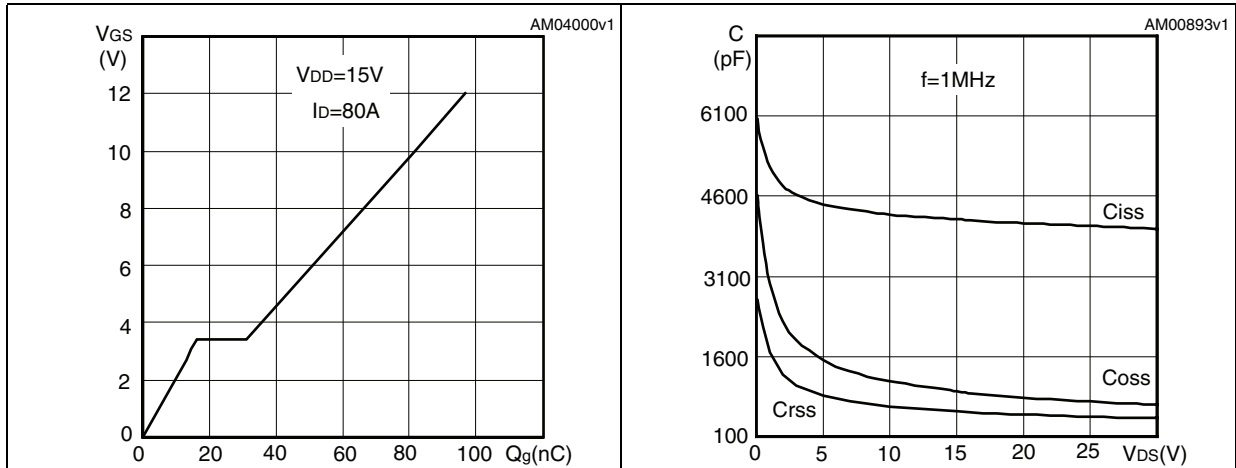


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

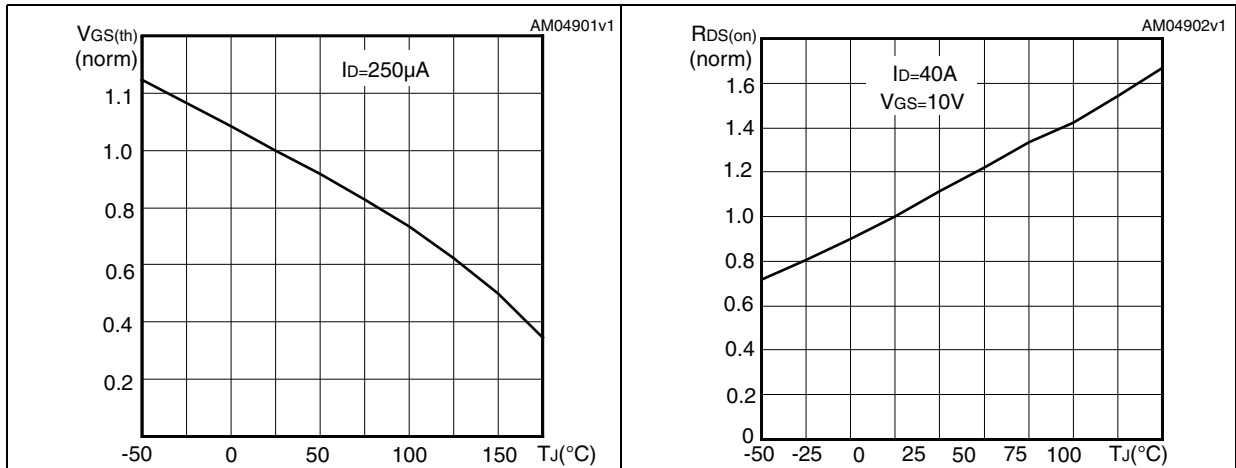
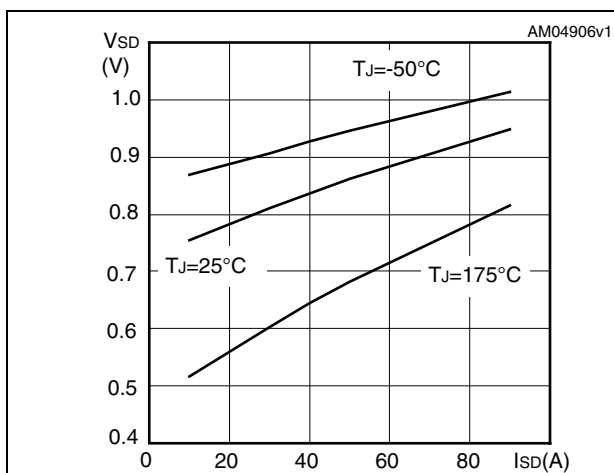


Figure 12. Source-drain diode forward characteristics



3 Test circuit

Figure 13. Switching times test circuit for resistive load

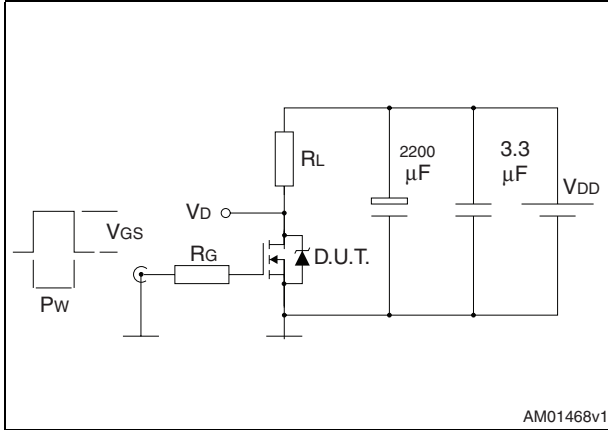


Figure 14. Gate charge test circuit

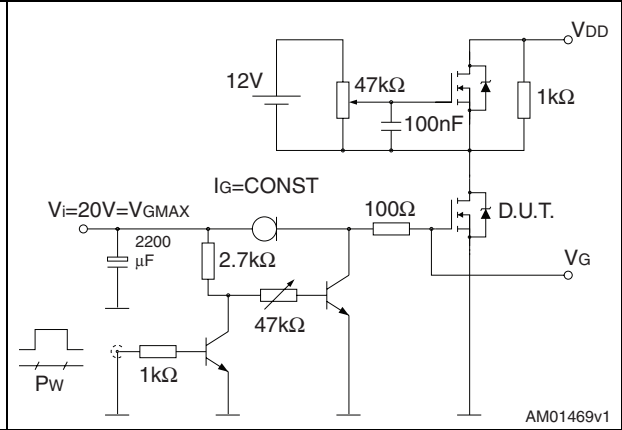


Figure 15. Test circuit for inductive load switching and diode recovery times

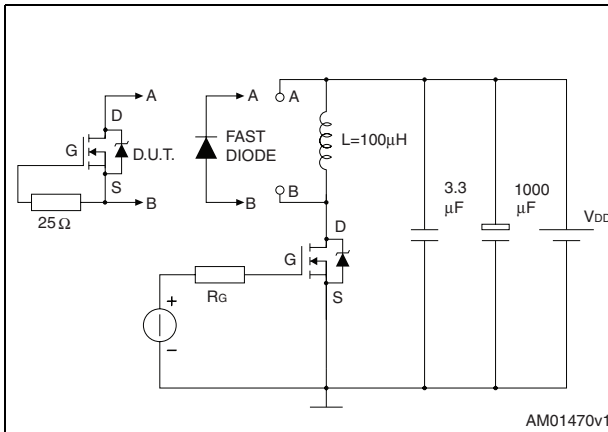


Figure 16. Unclamped Inductive load test circuit

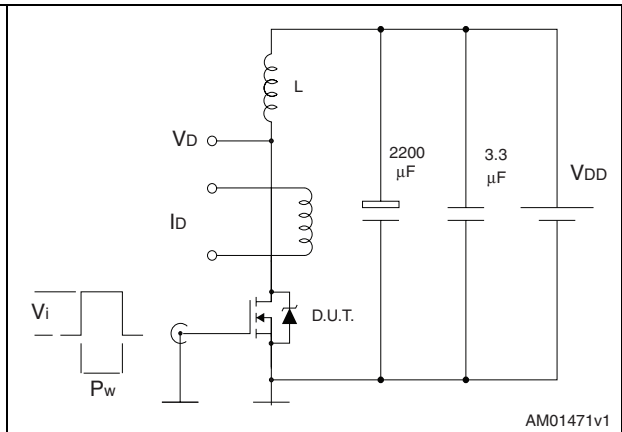


Figure 17. Unclamped inductive waveform

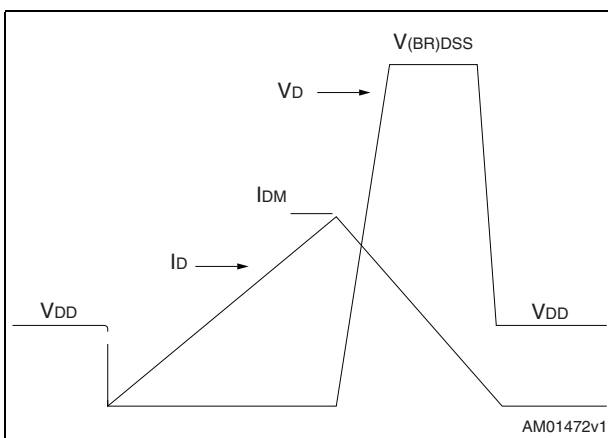


Figure 18. Switching time waveform

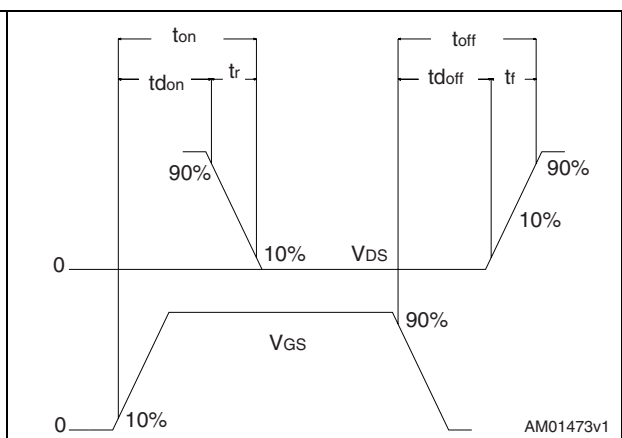
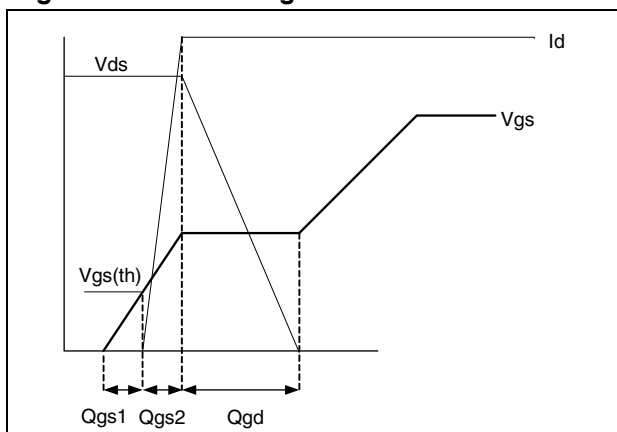


Figure 19. Gate charge waveform

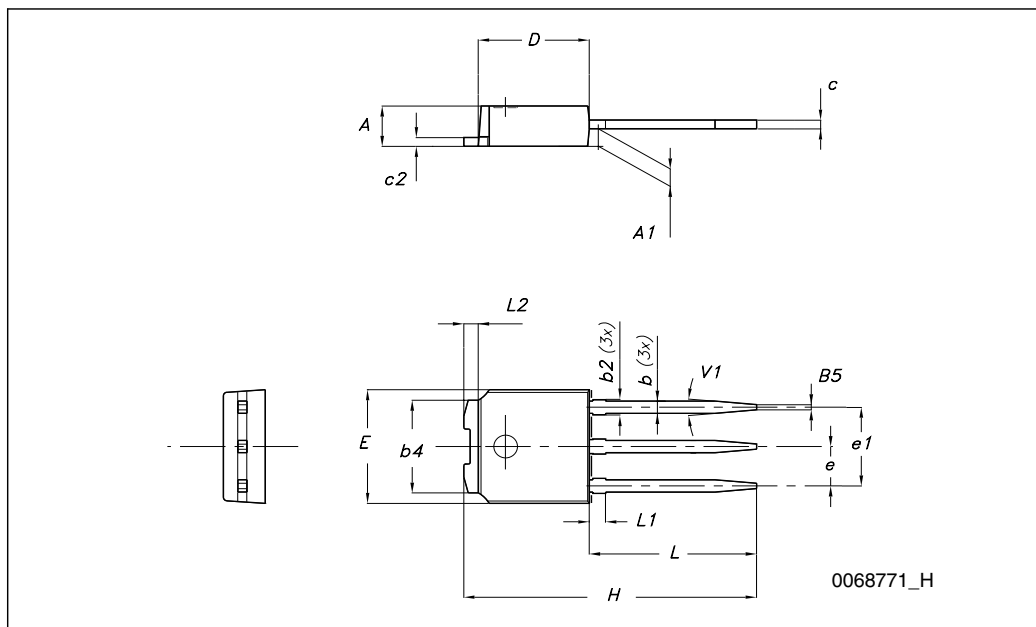


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

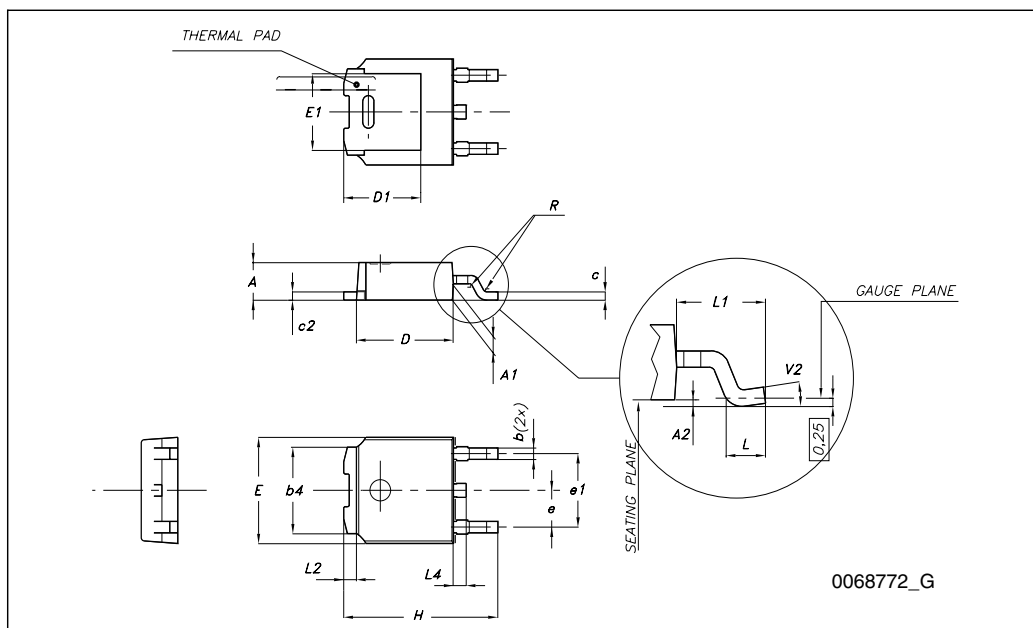
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



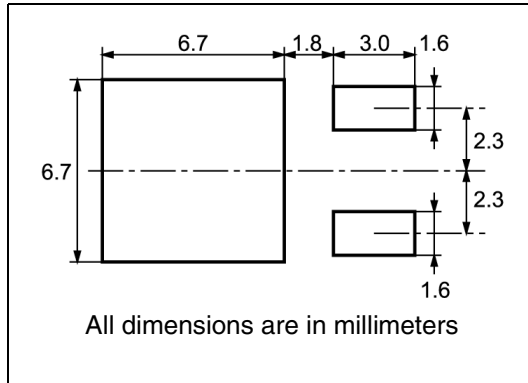
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

BASE QTY

2500

BULK QTY

2500

TOP COVER TAPE

User Direction of Feed

Center line of cavity

Bending radius R min.

FEED DIRECTION

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

TRL

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
01-Dec-2008	1	First release
20-Jul-2009	2	– Document status promoted from preliminary data to datasheet – Added new package, mechanical data: TO-220
10-Sep-2009	3	Q_{gs} and Q_{gd} values have been modified on Table 5: Dynamic

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